In the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Canceled).

2. (Canceled).

3. (Canceled).

4. (Canceled).

5. (Canceled).

6. (Canceled).

7. (Canceled).

8. (Canceled).

9. (Canceled).

10. (New) A reflective crystal display device comprising:

a semiconductor substrate;

at least one pair of pixel switching transistor and a capacitor formed on the semiconductor substrate and electrically isolated from each other;

a first interlayer insulating layer formed on the pixel switching transistor and the capacitor;

a wiring layer formed on the first interlayer insulating layer;

a second interlayer insulating layer formed over the wiring layer;

a light shielding layer formed on the second interlayer insulating layer, the light shielding layer being divided into a plurality of layer portions by gaps;

a third interlayer insulating layer formed over the light shielding layer;

at least one pixel electrode formed on the third interlayer insulating layer;

a common electrode formed over the pixel electrode;

a liquid crystal layer provided between the pixel electrode and the common electrode;

a light-transmissive substrate formed on the common electrode; and

at least one anti-reflection layer formed on the light shielding layer, the anti-reflection layer being a double layer of a metallic film and a film including Si that exhibits a refraction index different from a refraction index of the third interlayer insulating layer, the film including Si covering the gaps of the light shielding layer.

11. (New) The reflective liquid crystal display device according to claim 10, wherein the metallic film is a metallic nitride film.

12. (New) The reflective liquid crystal display device according to claim 10, wherein the metallic film is a titanium film.

13. (New) The reflective liquid crystal display device according to claim 12, wherein the titanium film is a titanium nitride film.

14. (New) The reflective liquid crystal display device according to claim 10, wherein the film including Si is silicon oxynitride film.

15. (New) The reflective liquid crystal display device according to claim 14, wherein the refraction index of the silicon oxynitride film is in the range from 1.7 to 1.9.

16. (New) The reflective liquid crystal display device according to claim 14, wherein a thickness of the silicon oxynitride film is in the range from 400 to 600 Å.

17. (New) The reflective liquid crystal display device according to claim 10, wherein a thickness of the metallic film is small than 300 nm.

18. (New) The reflective liquid crystal display device according to claim 10, wherein a thickness of the metallic film is about 800 Å.

19. (New) A reflective liquid crystal display device comprising:

a semiconductor substrate;

at least one pair of pixel switching transistor and a capacitor formed on the semiconductor substrate and electrically isolated from each other;

a first interlayer insulating layer formed on the pixel switching transistor and the capacitor;

a wiring layer formed on the first interlayer insulating layer, the wiring layer being divided into a plurality of layer portions by gaps;

a second interlayer insulating layer formed over the wiring layer;

a light shielding layer formed on the second interlayer insulating layer;

a third interlayer insulating layer formed over the light shielding layer;

at least one pixel electrode formed on the third interlayer insulating layer;

a common electrode formed over the pixel electrode;

a liquid crystal layer provided between the pixel electrode and the common electrode;

a light-transmissive substrate formed on the common electrode; and

at least one anti-reflection layer formed on the wiring layer, the anti-reflection layer being a double layer of a metallic film and a film including Si that exhibits a refraction index different from a refraction index of the third interlayer insulating layer, the film including Si covering the gaps of the wiring layer.

20. (New) The reflective liquid crystal display device according to claim 19, wherein the metallic film is a metallic nitride film.

21. (New) The reflective liquid crystal display device according to claim 19, wherein the metallic film is a titanium film.

22. (New) The reflective liquid crystal display device according to claim 21, wherein the titanium film is a titanium nitride film.

23. (New) The reflective liquid crystal display device according to claim 19, wherein the film including Si is silicon oxynitride film.

24. (New) The reflective liquid crystal display device according to claim 23, wherein the refraction index of the silicon oxynitride film is in the range from 1.7 to 1.9.

25. (New) The reflective liquid crystal display device according to claim 23, wherein a thickness of the silicon oxynitride film is in the range from 400 to 600 Å.

26. (New) The reflective liquid crystal display device according to claim 19, wherein a thickness of the metallic film is smaller than 300 nm.

27. (New) The reflective liquid crystal display device according to claim 19, wherein a thickness of the metallic film is about 800 Å.

28. (New) A reflective crystal display device comprising:

a semiconductor substrate;

at least one pair of pixel switching transistor and a capacitor formed on the semiconductor substrate and electrically isolated from each other;

a first interlayer insulating layer formed on the pixel switching transistor and the capacitor;

a wiring layer formed on the first interlayer insulating layer, the wiring layer being divided into a plurality of layer portions by gaps;

a second interlayer insulating layer formed over the wiring layer;

a light shielding layer formed on the second interlayer insulating layer, the light shielding layer being divided into a plurality of layer portions by gaps;

a third interlayer insulating layer formed over the light shielding layer;

at least one pixel electrode formed on the third interlayer insulating layer;

a common electrode formed over the pixel electrode;

a liquid crystal layer provided between the pixel electrode and the common electrode;

a light-transmissive substrate formed on the common electrode;

a first anti-reflection layer formed on the wiring layer, the first anti-reflection layer being a double layer of a metallic film and a first film including Si that exhibits a refraction index different from a refraction index of the third interlayer insulating layer, the first film including Si covering the gaps of the wiring layer; and

a second anti-reflection layer formed on the light shielding layer, the second anti-reflection layer being a double layer of a metallic film and

a second film including Si that exhibits a refraction index different from a refraction index of the third interlayer insulating layer, the second film including Si covering the gaps of the light shielding layer.

29. (New) The reflective liquid crystal display device according to claim 28, wherein each metallic film is a metallic nitride film.

30. (New) The reflective liquid crystal display device according to claim 28, wherein each metallic film is a titanium film.

31. (New) The reflective liquid crystal display device according to claim 30, wherein the titanium film is a titanium nitride film.

32. (New) The reflective liquid crystal display device according to claim 28, wherein each film including Si is silicon oxynitride film.

33. (New) The reflective liquid crystal display device according to claim 32, wherein the refraction index of the silicon oxynitride film is in the range from 1.7 to 1.9.

34. (New) The reflective liquid crystal display device according to claim 32, wherein a thickness of the silicon oxynitride film is in the range from 400 to 600 Å.

35. (New) The reflective liquid crystal display device according to claim 28, wherein a thickness of each metallic film is smaller than 300 nm.

36. (New) The reflective liquid crystal display device according to claim 28, wherein a thickness of each metallic film is bout 800 Å.